

ESE532: System-on-a-Chip Architecture

Day 22: November 17, 2021
Estimating Chip Area and Costs



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Today

- Part 1: Chip Costs from Area
- Part 2: Chip Area
 - IO
 - Interconnect – Rent's Rule
 - Infrastructure
- Part 3: Some Areas

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Message

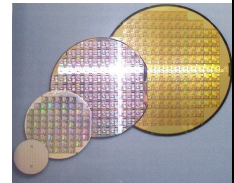
- First order:
 - Chip cost proportional to Area
 - Area = Sum(Area(Components))
- But appreciate the simplification:
 - Yield makes cost superlinear in area
 - I/O, Interconnect, infrastructure
 - Can make Area > Sum(Area(Components))

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Wafer Cost

- Incremental cost of producing a silicon wafer is fixed for a given technology
 - Independent of the specific design
 - E.g. \$4,000
- Can fill wafer with copies of chip



By German Wikipediabiatch, original upload 7. Okt 2004 by Stahlkocher de:Bild:Wafer 2 Zoll bis 8 Zoll.jpg, CC BY-SA 3.0, <https://commons.wikimedia.org/w/index.php?curid=928106>

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16nm Wafer Costs

	16/14nm FinFET		14nm FD SOI	
	\$	%	\$	%
Depreciation	2,303.94	58.79	1,972.26	53.24
Equipment maintenance	581.42	14.84	445.32	12.02
Direct labor	64.78	1.65	45.52	1.23
Indirect labor	238.76	6.09	208.36	5.62
Facilities	232.47	5.93	189.37	5.11
Wafer cost	99.93	2.55	475.00	12.82
Consumables	359.28	9.17	331.47	8.95
Monitor wafers	38.62	0.99	37.24	1.01
TOTAL Unyielded wafer cost	3,919.20	100.00	3,704.54	100.00
Line yield (%)	96.03	--	97.96	--
TOTAL Yielded wafer cost	4,081.22	--	3,781.69	--

Source: https://www.eetimes.com/author.asp?section_id=36&doc_id=1329887

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Preclass 1

- Rough cost per mm of silicon?
 - \$4000 for 300mm wafer

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Implication

- Raw silicon die cost is roughly proportional to area
 - Larger the die, the fewer we get on the wafer

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...but

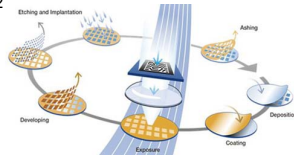
- Limits to how big we can make chips
 - Manufacturers are prepared to create
 - Can be reliably manufactured
- ...and how small we can make chips
 - I/O pads
 - Cutting/handling/markings

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Imaging

- Limit to how large optical imaging supports
- Reticle – imagable region for photo lithography
 - Around 600mm^2



Source: <https://www.asml.com/the-asml-exposure-apparatus-is-the-most-expensive-and-complex-step-in-the-chip-fabrication-process-what-is-involved-in-the-lithography-business/ja/281457ad-44709>

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Yield

- Chips won't be manufactured perfectly
 - Dust particles can impact imaging
 - Manufacturing processes are statistical
- If chips must be defect-free,
 - larger chips are more likely to have defects than smaller chips

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Simple Yield Model

- Probability of a region being perfect
 - E.g. probability of one sq. mm being defect-free
- Chip yields if its entire area is defect free

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Chip Yield

- P = defect-free probability per sq. mm
- What is probability a chip of A sq. mm yields (symbolic) ?

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Preclass 2

- $P=0.99$
- Probability of yield for
– 10 mm², 50 mm², 100 mm², 500 mm²

Area (mm ²)	Yield Rate
10	
50	
100	
500	

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Preclass 2

- $P=0.99$
- Probability of yield for
– 10 mm², 50 mm², 100 mm², 500 mm²

Area (mm ²)	Yield Rate
10	0.90
50	0.60
100	0.37
500	0.0066

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Yielded Die

- For a yield rate, Y, how many raw die need to manufacture per yielded die?

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Preclass 3

- $P=0.99$
- Die cost for:
– 10 mm², 50 mm², 100 mm², 500 mm²

Area	Raw Cost	Yield Rate	Cost/Yielded Chip
10		0.90	
50		0.60	
100		0.37	
500		0.0066	

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Preclass 3

- $P=0.99$ $0.06 / \text{mm}^2$
- Die cost for:
– 10 mm², 50 mm², 100 mm², 500 mm²

Area	Raw Cost	Yield Rate	Cost/Yielded Chip
10	0.60	0.90	
50	3.00	0.60	
100	6.00	0.37	
500	30.00	0.0066	

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Preclass 3

- $P=0.99$ $0.06 / \text{mm}^2$
- Die cost for:
– 10 mm², 50 mm², 100 mm², 500 mm²

Area	Raw Cost	Yield Rate	Cost/Yielded Chip
10	0.60	0.90	0.67
50	3.00	0.60	5.00
100	6.00	0.37	16.22
500	30.00	0.0066	4500

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Yielded Die Cost

$$Cost = \frac{Raw}{Yield} = \frac{A * Cost/mm^2}{P^A}$$

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Yielded Die Cost

$$Cost = \frac{Raw}{Yield} = \frac{A * Cost/mm^2}{P^A}$$

- Ultimately exponential in Area
- Means
 - Expensive above knee in exponential curve
 - Close to linear below knee in curve
- E.g.
 - Below $P^A=0.5$
 - effect of Yield term is less than 2

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Design Dependent Cost

- P can be design dependent
 - More aggressive designs have higher defect rates
 - Can tune design to ease manufacturing
- Contrast with point that wafer manufacture cost independent of design

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Slightly Fuller Story

- Chip cost = die + test + package

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Test

- Testing costs proportional to test time
 - Time on expensive test unit
 - Depends on complexity of tests need to run
 - Can motivate spending silicon area on on-chip test structures to reduce
- Can dominate on small chips or complex testing

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Packaging

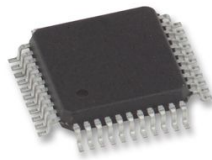
- Pay for density and performance

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Plastic Packages

- Simple plastic packages cheap
 - Limited number of pins
 - Limited to perimeter
 - Limited heat removal (few Watts)
 - Can be large (due to pins)
 - Higher inductance on pins



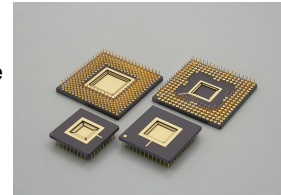
http://wiki.electrooons.com/doku.php?id=ic_packages

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Ceramic Packages

- Better thermal characteristics
 - Add heat-sink, tolerate hotter chips
 - To 100 W
 - More pins
 - More expensive



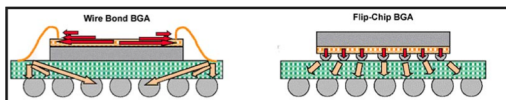
Source: https://www.ngkntk.co.jp/english/product/semiconductor_packages/htcc.html

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Flip Chip Packages

- Support Area-IO
 - More, denser pins
 - Smaller die if IO limited
 - Lower inductances
 - Smaller packaged chip

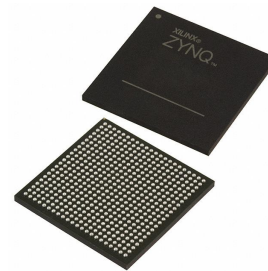


Source: <http://mantravlsi.blogspot.com/2014/10/flip-chip-and-wire-bonding.html>

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Zynq Land Grid Package



SBVA 484 – flip chip, Ball-Grid Array (UG 1075)

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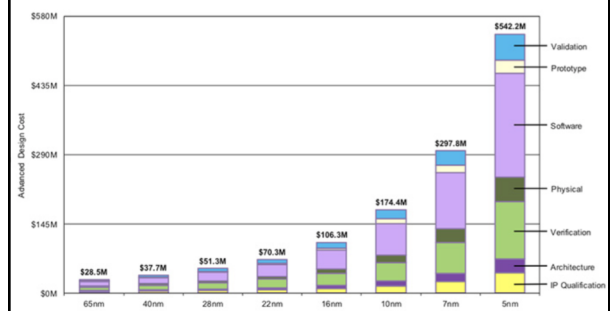
Don't Forget NRE

- This is all about recurring costs
- Cost = RecurringCost + (NRE/NumParts)
- NRE
 - Mask costs in millions
 - Design costs in 10s to 100s of millions

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Bonus: Chip Design Costs



<https://wccftech.com/apple-5nm-3nm-cost-transistors/>

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Putting Together

- 100mm² die -- \$5.6 raw
 - Maybe \$6--16 yielded -- call it \$7
- NRE \$100 M -- \$1
 - Sell 100 M units
- Put in \$1 package -- \$1
- Test -- \$1
- Total: \$10

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Price vs. Cost

- ...and this is all about **cost**
 - What it takes to manufacture
- Price
 - What people will pay for it
- Profit = Price - Cost

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Area

Part 2

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Area

- Simple story
 - Sum up component areas

$$A = \sum_i A_i$$

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Too Simplistic

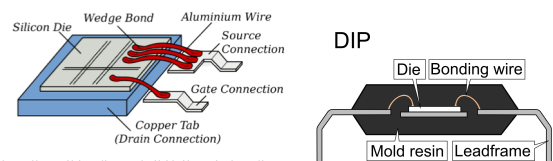
- Area may be driven by
 - I/O
 - Interconnect
- Will need to pay for infrastructure
 - Clocking, Power
 - ...maybe linear overhead factor

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I/O Pads

- Must go on edge for wire bonding
 - Esp. for cheap packages



Src: <http://en.wikipedia.org/wiki/File:Wirebonding2.svg>

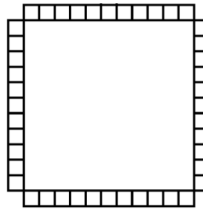
Source: https://commons.wikimedia.org/wiki/File:DIP_package_sideview.PNG

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Pad Ring

- Pads must go on side of chip
- Pad spacing large to permit bonding
- I/O pads may set lower bound on chip size

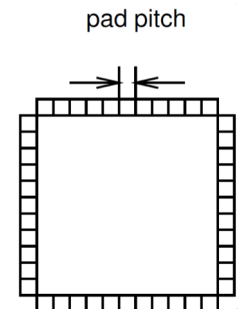


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Preclass 4

- 400 pads
- 25µm pad spacing
- Square chip dimensions?



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I/O Limits

- Perimeter grows as 4s
- Area grows as s²
- Area grows (NumIO/4)²
- IO may drive chip area

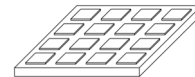
$$A = \text{Max} \left(\left(\sum_i A_i \right), \left(\frac{\text{NumIO}}{4 \times \text{PadPitch}} \right)^2 \right)$$

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Area I/O

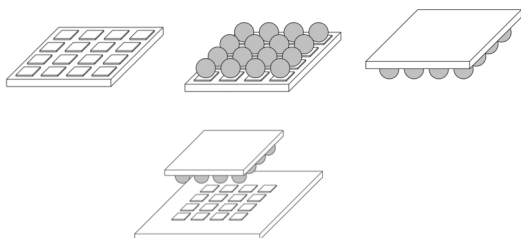
- Put I/O in grid over chip
- I/O pads still large and take up space
- Avoid perimeter scaling
- Requires more expensive flip-chip package



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Flip Chip I/O

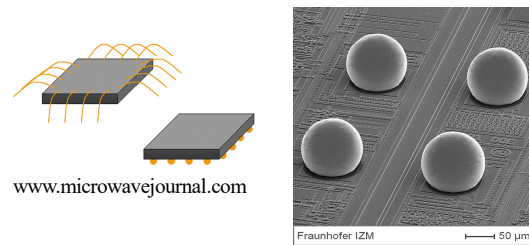


Source: https://en.wikipedia.org/wiki/Flip_chip

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Flip Chip, Area IO



www.microwavejournal.com

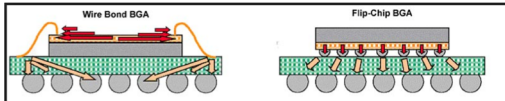
http://www.izm.fraunhofer.de/en/abteilungen/high_density_interconnect/waferlevelpackaging/arbeitsgebiete/arbeitsgebiet1.html

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Flip Chip Packages

- Support Area-IO
 - More, denser pins
 - Smaller die if IO limited
 - Lower inductances
 - Smaller packaged chip



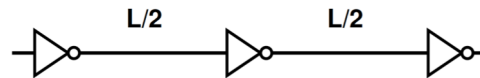
Source: <http://mantravlsi.blogspot.com/2014/10/flip-chip-and-wire-bonding.html>

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Interconnect

- Long wires need buffering
- Buffers take up space
 - Weren't in simple accounting of logic and memory blocks



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Interconnect

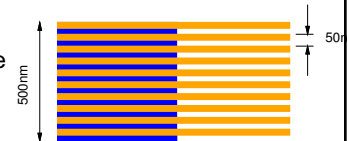
- Wires take up space
- Similar issue to pad I/O
 - Wires crossing into region grow as perimeter
 - Logic inside grows as area
- Region size may be dictated by wires entering/leaving

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Wiring Requirements

- Wires 50nm pitch
- Gates 500nm on side
 - (500nm x 500nm)
- How many wires fit across the side of one gate?

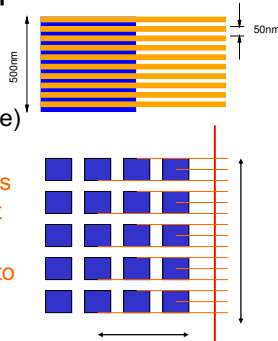


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Wiring Requirements

- Wires 50nm pitch
- Gates 500nm on side
 - (500nm x 500nm)
- Wires/gate side (prev slide)
- If have SxS gate on left, how many wires can cross over the line of S gates at the right?
- What if need more wires to cross to right?

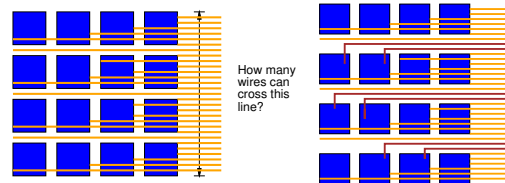


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Need More Wires

- What if need more wires to cross to right?

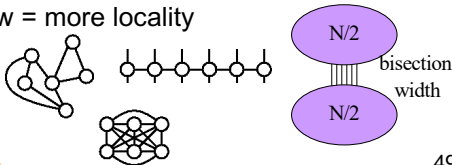


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Bisection Width

- Partition design into two equal size halves
 - Minimize wires (nets) with ends in both halves
- Number of wires crossing is **bisection width**
 - Information crossing
- lower bw = more locality



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Rent's Rule

- If we recursively bisect a graph, attempting to minimize the cut size, for an N-node graph, we typically get:

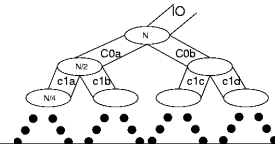
$$BW=IO = c N^p$$

$$-0 \leq p \leq 1$$

- $p \leq 1$ means many inputs come from within a partition

[Landman and Russo, IEEE TR Computers p1469, 1971]

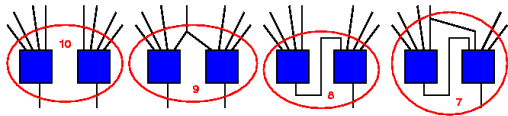
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Rent and Locality

- Rent and IO quantifying locality
 - local consumption
 - local fanout

$$IO = c N^p$$

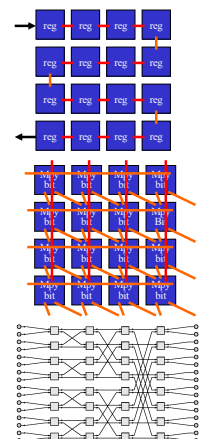


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Common Applications

- Rent $p=0$
 - Shift-register, 1D filter
- Rent $p=0.5$
 - Array multiplier
 - 2D Window Filter
 - nearest-neighbor
- Rent $p=1.0$
 - FFT, Sort

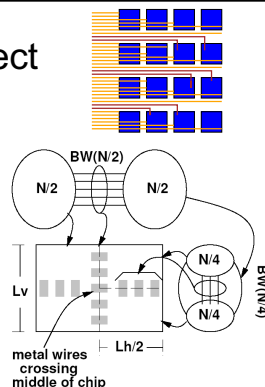


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VLSI Interconnect Area

- Bisection width is lower-bound on IC width
 - When wire dominated, may be tight bound
- (recursively)
- Rent's Rule tells us how big our chip must be



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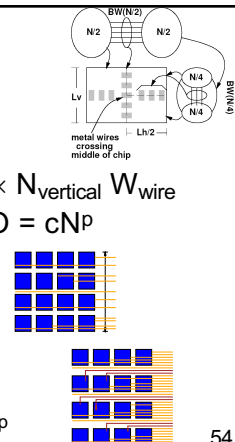
As a function of Bisection

- $A_{chip} \geq N \times A_{gate}$
- $A_{chip} \geq N_{horizontal} W_{wire} \times N_{vertical} W_{wire}$
- $N_{horizontal} = N_{vertical} = IO = c N^p$
- $A_{chip} \geq (cN)^{2p}$
- If $p < 0.5$

$$A_{chip} \propto N$$

- If $p > 0.5$

$$A_{chip} \propto N^{2p}$$



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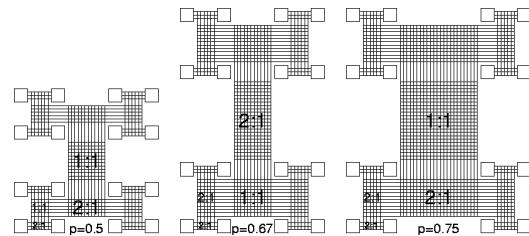
In terms of Rent's Rule

- If $p < 0.5$, $A_{\text{chip}} \propto N$
- If $p > 0.5$, $A_{\text{chip}} \propto N^{2p}$
- **Typical** designs have $p > 0.5$
 - **interconnect dominates**
 - $A_{\text{chip}} > \sum A_{\text{elements}}$

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Rent Network Richness



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Infrastructure: Clocking

- PLL (Phased-Lock-Loop) to generate and synchronize clock
- Clock drivers are big (drive big load)
- Need buffering all over chip

$$A = F_{\text{infra}} \times \sum_i A_i$$

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Infrastructure: Power

- Need many I/O Pads
 - Carry current
 - Keep inductance low
- Wires to distribute over chip
- Maybe
 - Capacitance to stabilize power
 - Voltage converters

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Area

$$A = F_{\text{infra}} \times \sum_i A_i$$

- Mostly sum of components, but...
- Area may be driven by
 - I/O
 - Interconnect $A \geq N^{2p}$
- Will need to pay for infrastructure
 - Clocking, Power
 - Include as components
 - Then linear factor for distribution

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Some Areas

Part 3

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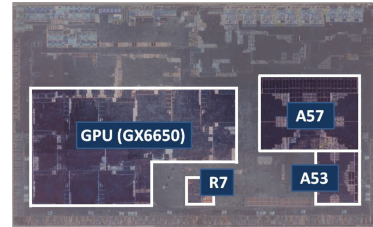
Processor Areas

- ARM Cortex A53 about 2mm^2 in 28nm
 - Zynq UltraScale+ processor
 - SuperScalar core
- A5 (scalar) about 0.25mm^2
- A9 (superscalar) about 1mm^2
- A15 (higher performance) about 3mm^2
- A57 (big core to A53 little) about 3mm^2
- A72 (Amazon a1) about 4.6mm^2
 - (ARM claim 1.15mm^2 in 16nm FinFet)

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R-Car H3 from Rensas Quad A57, Quad A53



https://en.wikichip.org/wiki/arm_holdings/microarchitectures/cortex-a53

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Zynq Compute Blocks

Crude estimate, including interconnect

- 2000 6-LUTs per sq. mm
- DSP Block ~ 0.1 sq. mm

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CACTI

- Standard program for modeling memories and caches
 - More sophisticated version of the simple modeling we've been doing

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CACTI – Memories on Zynq

- 32nm (closest technology it models to 28nm in Zynq)
- 36Kb BRAMs 0.025mm^2
 - 2 port, 72b output
- ARM L1 cache 0.08mm^2
 - 32KB 4-way associative
- ARM L2 cache 1.5mm^2
 - 512KB 8-way associative
 - (older, not yours)

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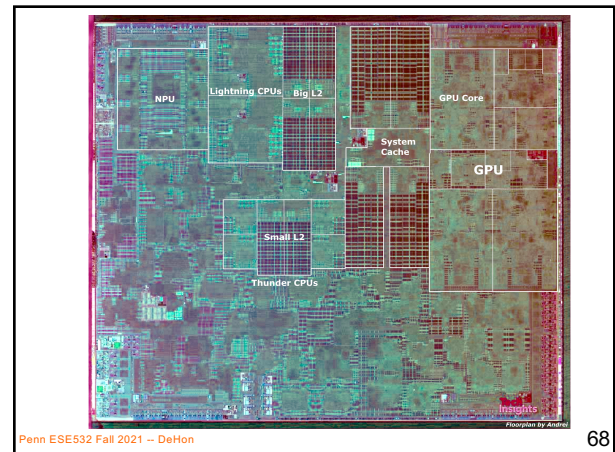
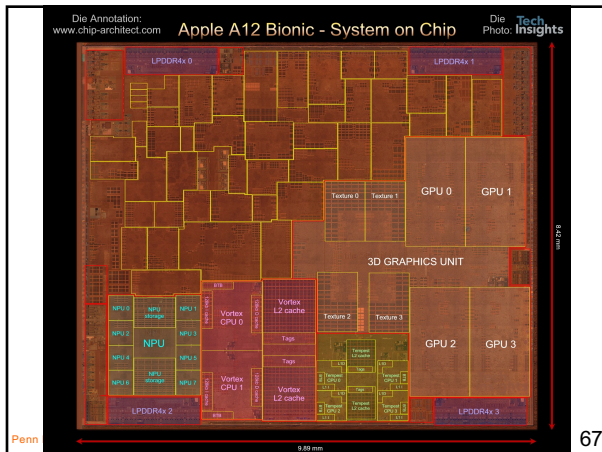
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Zynq Component Estimates

- 6-LUT 0.0005mm^2
- DSP Block 0.1mm^2
- 36Kb BRAMs 0.025mm^2
- ARM L1 cache 0.08mm^2
- ARM L2 cache (512KB, 8-way) 1.5mm^2
- ARM Cortex A53 2.0mm^2

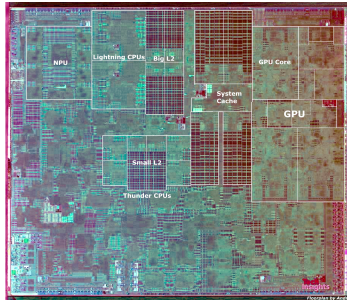
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Apple A13 Bionic

- 98mm², 7nm
- 8.5 Billion Tr.
- iPhone 11 +
- 6 ARM cores
 - 2 fast (2.6GHz)
 - 4 low energy
- 4 custom GPUs
- Neural Engine
 - 5 Trillion ops/s?



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A13 Die Areas

- https://en.wikipedia.org/wiki/Apple_A13

SoC	A13 (7 nm)	A12 (7 nm)
Process Node	TSMC N7P	TSMC N7
Total Die	98.48	83.27
Big Core	2.61	2.07
Small Core	0.58	0.43
CPU Complex (incl. cores)	13.47	11.16
GPU Core	3.25	3.23
GPU Total	15.28	14.88
NPU	2.09	1.23

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Big Ideas $A = F_{infra} \times \sum_i A_i$

- First order:
 - Chip cost proportional to Area
 - Area = Sum(Area(Components))
- But appreciate the simplification:
 - Yield makes cost superlinear in area
 - Limited range over which “linear” accurate
 - I/O, Interconnect, infrastructure
 - Can make Area > Sum(Area(Components))

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Admin

- Reading for Monday on Web
- P3 due Friday
- P4 posted
 - due 2 weeks, next Friday Thanksgiving break

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